

FS10KMJ-06

HIGH-SPEED SWITCHING USE

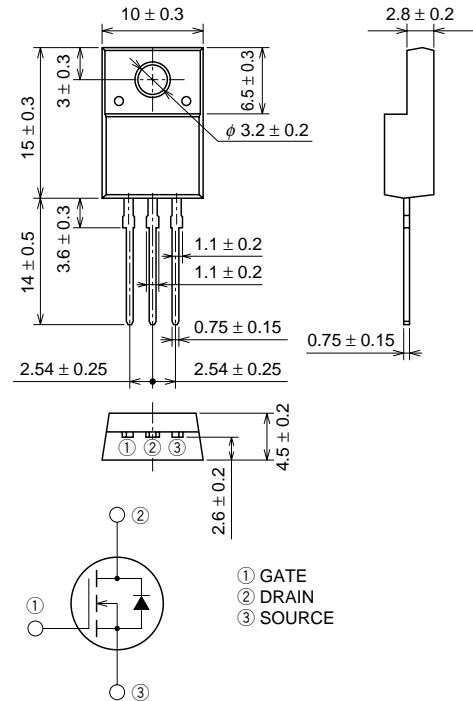
FS10KMJ-06



- 4V DRIVE
- V_{DSS} 60V
- r_{DS (ON)} (MAX) 70mΩ
- I_D 10A
- Integrated Fast Recovery Diode (TYP.) 55ns
- V_{iso} 2000V

OUTLINE DRAWING

Dimensions in mm



TO-220FN

APPLICATION

Motor control, Lamp control, Solenoid control
DC-DC converter, etc.

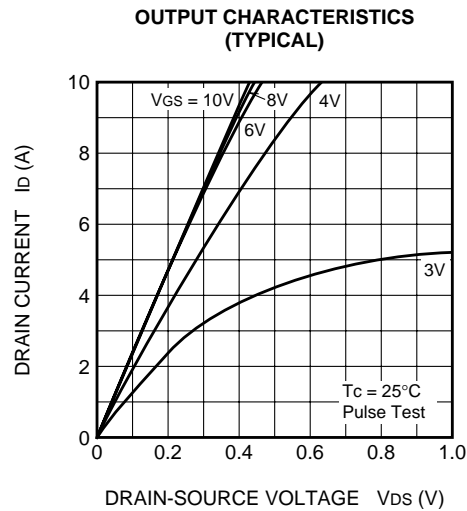
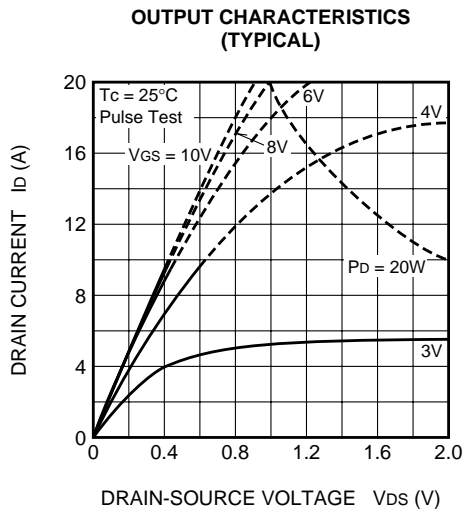
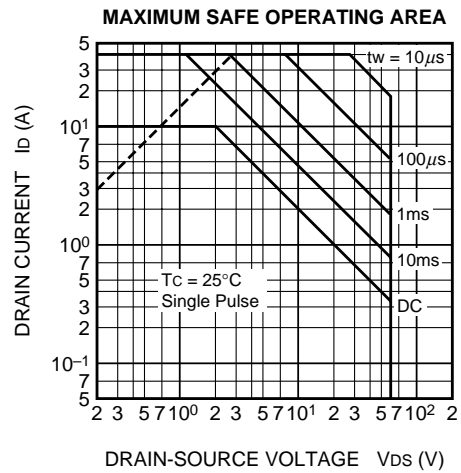
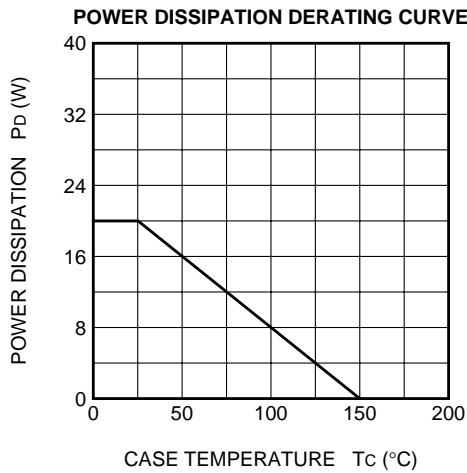
MAXIMUM RATINGS (T_c = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
V _{DSS}	Drain-source voltage	V _{GS} = 0V	60	V
V _{GSS}	Gate-source voltage	V _{DS} = 0V	±20	V
I _D	Drain current		10	A
I _{DM}	Drain current (Pulsed)		40	A
I _{DA}	Avalanche drain current (Pulsed)	L = 100μH	10	A
I _S	Source current		10	A
I _{SM}	Source current (Pulsed)		40	A
P _D	Maximum power dissipation		20	W
T _{ch}	Channel temperature		-55 ~ +150	°C
T _{stg}	Storage temperature		-55 ~ +150	°C
V _{iso}	Isolation voltage	AC for 1minute, Terminal to case	2000	V
—	Weight	Typical value	2.0	g

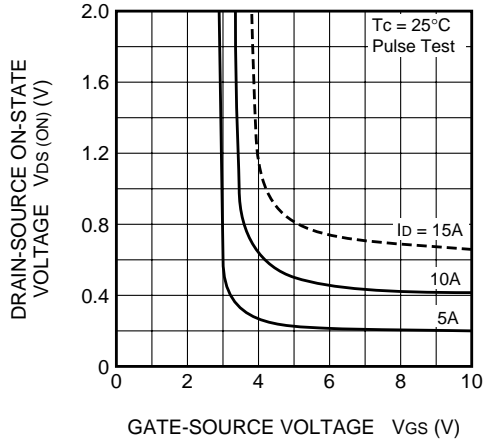
ELECTRICAL CHARACTERISTICS (Tch = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V (BR) DSS	Drain-source breakdown voltage	Id = 1mA, VGS = 0V	60	—	—	V
IGSS	Gate-source leakage current	VGS = ±20V, VDS = 0V	—	—	±0.1	μA
IDSS	Drain-source leakage current	VDS = 60V, VGS = 0V	—	—	0.1	mA
VGS (th)	Gate-source threshold voltage	Id = 1mA, VDS = 10V	1.0	1.5	2.0	V
rDS (ON)	Drain-source on-state resistance	Id = 5A, VGS = 10V	—	53	70	mΩ
rDS (ON)	Drain-source on-state resistance	Id = 5A, VGS = 4V	—	66	91	mΩ
VDS (ON)	Drain-source on-state voltage	Id = 5A, VGS = 10V	—	0.265	0.35	V
yfs	Forward transfer admittance	Id = 5A, VDS = 5V	—	13	—	S
Ciss	Input capacitance	VDS = 10V, VGS = 0V, f = 1MHz	—	800	—	pF
Coss	Output capacitance		—	190	—	pF
Crss	Reverse transfer capacitance		—	80	—	pF
td (on)	Turn-on delay time	VDD = 30V, Id = 5A, VGS = 10V, RGEN = RGS = 50Ω	—	14	—	ns
tr	Rise time		—	17	—	ns
td (off)	Turn-off delay time		—	65	—	ns
tf	Fall time		—	40	—	ns
VSD	Source-drain voltage	IS = 5A, VGS = 0V	—	1.0	1.5	V
Rth (ch-c)	Thermal resistance	Channel to case	—	—	6.25	°C/W
trr	Reverse recovery time	IS = 10A, dis/dt = -100A/μs	—	55	—	ns

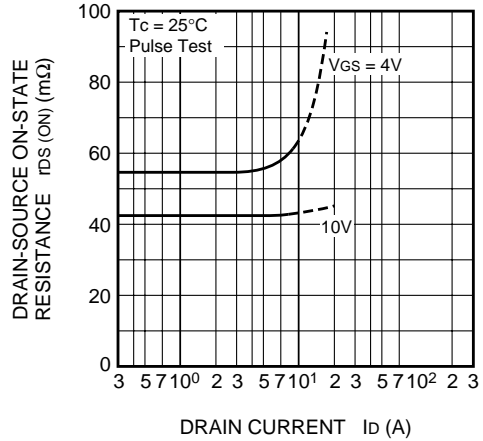
PERFORMANCE CURVES



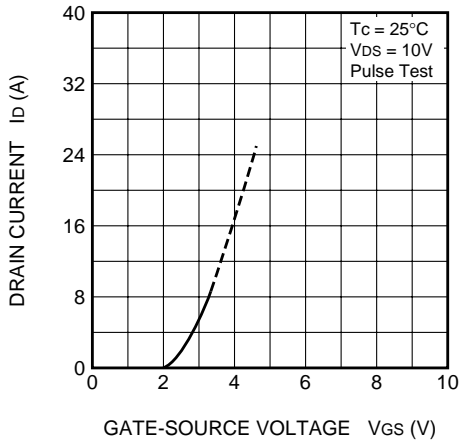
ON-STATE VOLTAGE VS. GATE-SOURCE VOLTAGE (TYPICAL)



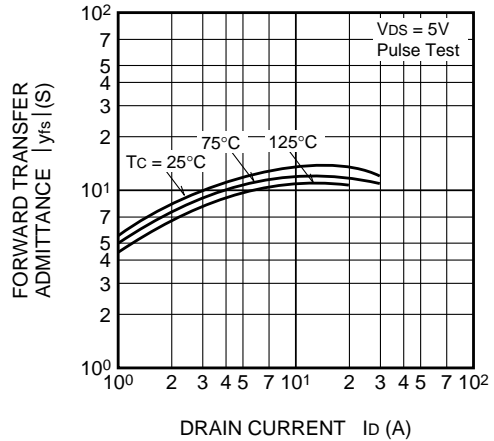
ON-STATE RESISTANCE VS. DRAIN CURRENT (TYPICAL)



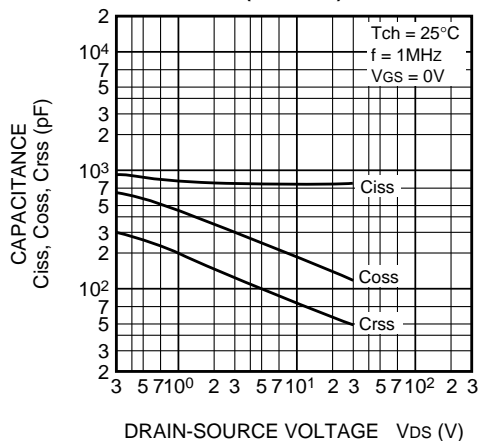
TRANSFER CHARACTERISTICS (TYPICAL)



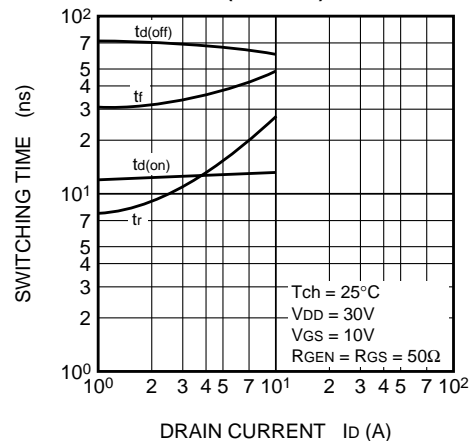
FORWARD TRANSFER ADMITTANCE VS. DRAIN CURRENT (TYPICAL)



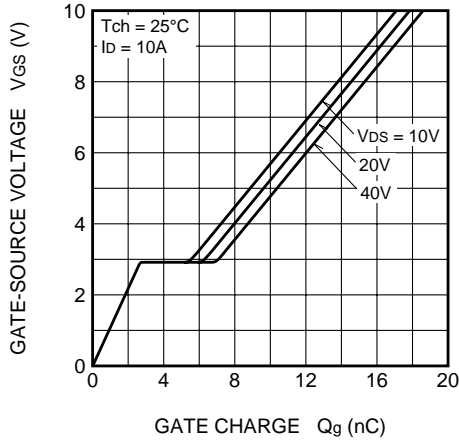
CAPACITANCE VS. DRAIN-SOURCE VOLTAGE (TYPICAL)



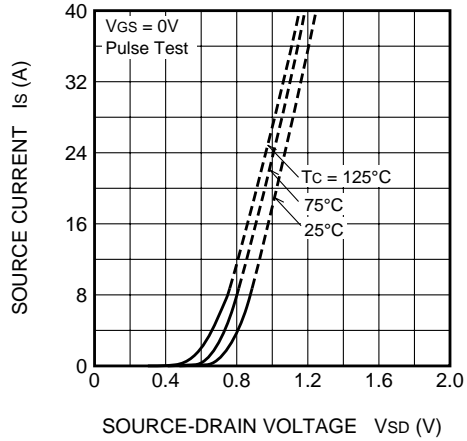
SWITCHING CHARACTERISTICS (TYPICAL)



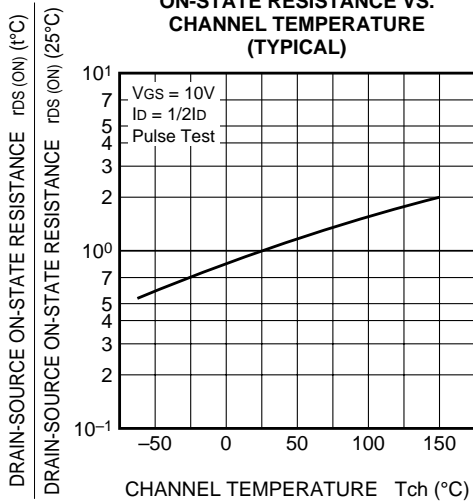
GATE-SOURCE VOLTAGE VS. GATE CHARGE (TYPICAL)



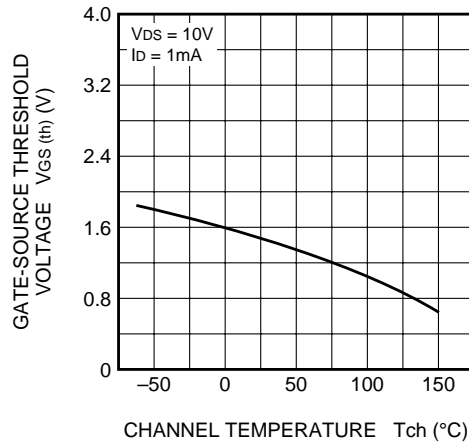
SOURCE-DRAIN DIODE FORWARD CHARACTERISTICS (TYPICAL)



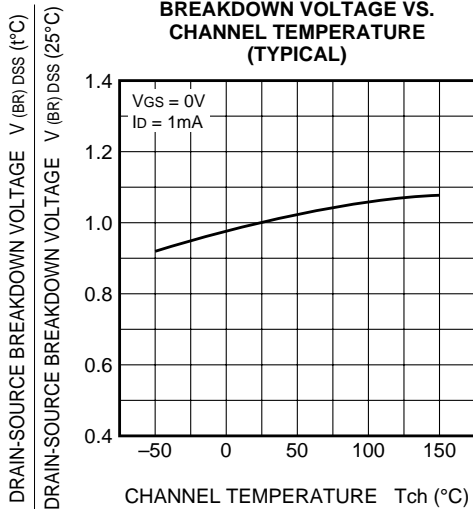
ON-STATE RESISTANCE VS. CHANNEL TEMPERATURE (TYPICAL)



THRESHOLD VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)



BREAKDOWN VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS

